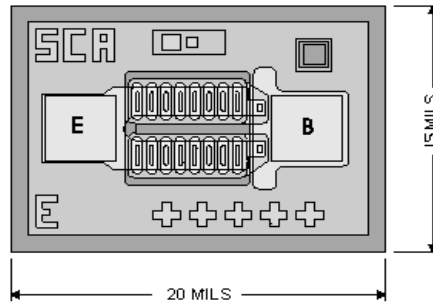


**Chip Type 2C3866A**  
**Geometry 1007**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N3866, 2N3866A**



[Request Quotation](#)

Chip type **2C3866A** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

2N3866A, 2N3866, 2N3866AUB, SD3866A, SD3866AF, SQ3866A, SQ3866AF

**Product Summary:**

**APPLICATIONS:** Designed for amplifier, frequency multiplier and oscillator applications. Suitable for output, driver and predriver stages in VHF and UHF equipment.

**Features: Special Characteristics:**

ft = 950 MHz (type) at 50 mA/15V

Mechanical Specifications		
Metallization	Top	Al - 15 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	3.4 mils x 3.0 mils
	Base	3.4 mils x 3.0 mils
Die Thickness	8 mils nominal	
Chip Area	15 mils x 20 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
T <sub>A</sub> = 25°C				
Parameter	Test conditions	Min	Max	Unit
BV <sub>CEO</sub>	I <sub>C</sub> = 5.0 mA	30	---	V dc
BV <sub>CBO</sub>	I <sub>C</sub> = 100 µA	55	---	V dc
BV <sub>CER</sub>	I <sub>C</sub> = 5.0 mA, R <sub>BE</sub> = 10 Ohms	55	---	V dc
BV <sub>EBO</sub>	I <sub>E</sub> = 100 µA	3.5	---	V dc
I <sub>CEO</sub>	V <sub>CE</sub> = 28 V, V <sub>EB</sub> = 2.0 V	---	20	µA
h <sub>FE1</sub>	I <sub>C</sub> = 360 mA dc, V <sub>CE</sub> = 5.0 V	5.0	---	---
h <sub>FE2</sub>	I <sub>C</sub> = 50 mA dc, V <sub>CE</sub> = 5.0 V	10	200	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 µs, duty cycle less than 2%.*